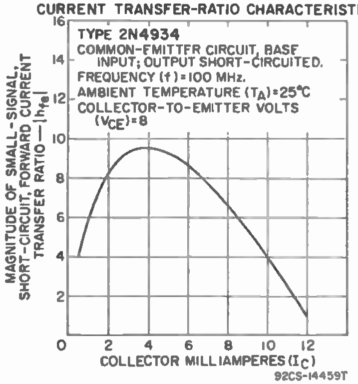
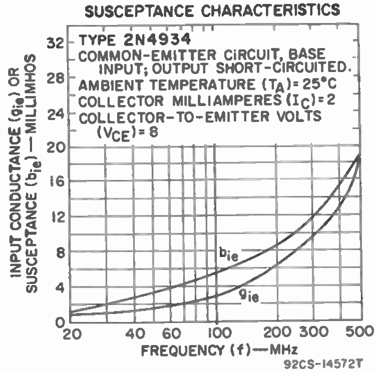
TYPICAL SMALL-SIGNAL FORWARD-CURRENT TRANSFER-RATIO CHARACTERISTIC



TYPICAL INPUT CONDUCTANCE AND SUSCEPTANCE CHARACTERISTICS



TRANSISTOR 2N4935

Si n-p-n epitaxial planar type used in vhf-uhf applications at frequencies up to 500 MHz. The terminal arrangement permits shielding between input and output terminals for superior high-frequency performance and greater circuit stability, particularly on printed-circuit boards. JEDEC TO-104, Outline No.26 (4-lead). Terminals: 1 - base, 2 - emitter, 3 - collector, 4 - connected to case. This type is identical with type 2N4934 except for the following items:

MAXIMUM RATINGS

Collector-to-Base Voltage	V_{CBO}	50	V
Collector-to-Emitter Voltage	V_{CEO}	40	V

CHARACTERISTICS

Collector-to-Base Breakdown Voltage (I_C = 0.001 mA, I_E = 0)	$V_{(BR)CBO}$	50	V
Collector-to-Emitter Breakdown Voltage (I_C = 1 mA, I_B = 0)	$V_{(BR)CEO}$	40	V
Static Forward-Current Transfer Ratio (V_{CE} = 8 V, I_C = 2 mA)	h_{FE}	60 to 200	
Magnitude of Small-Signal Forward-Current Transfer Ratio* (V_{CE} = 8 V, I_C = 2 mA, f = 1 kHz)	$\|h_{fe}\|$	70 to 225	
Collector-to-Base Time Constant* (V_{CB} = 8 V, I_E = −2 mA, f = 31.9 MHz)	$r_b'C_c$	1 to 6	ps
Small-Signal Power Gain, Amplifier, Unneutralized* (V_{CE} = 8 V, I_C = 2 mA, R_G and R_L = 50 Ω, f = 200 MHz)	G_{pe}	21 to 28	dB
Noise Figure* (V_{CE} = 8 V, I_C = 2 mA, R_S = 200 Ω, R_G and R_L = 50 Ω, f = 200 MHz)	NF	3 max	dB

* Lead 4 (case) grounded.

TRANSISTOR 2N4936

Si n-p-n epitaxial planar type used in vhf-uhf applications at frequencies up to 500 MHz. The terminal arrangement permits shielding between input and output terminals for superior high-frequency performance and greater circuit stability, particularly on printed-circuit boards. JEDEC TO-104, Outline No.26 (4-lead). Terminals: 1 - base, 2 - emitter, 3 - collector, 4 - connected to case. This type is identical with type 2N4935 except for the following items: